



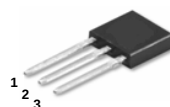
PTU13005G/PTD13005G

NPN Silicon Power Transistor
4.0 Amperes / 40 Watts

Switch Mode series NPN silicon Power Transistor

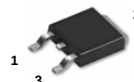
- High voltage, high speed power switching
- Suitable for switching regulator, inverters motor controls

PTU13005G
I-PAK(TO-251)



1. Base
2. Collector
3. Emitter

PTD13005G
D-PAK(TO-252)



1. Base
2. Collector
3. Emitter

Absolute Maximum Ratings TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	800	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current(DC)	I_C	4	A
Collector Current(Pulse)	I_{CP}	8	A
Base Current	I_B	2	A
Collector Dissipation($T_c=25^\circ\text{C}$)	P_C	40	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~150	°C

Electrical Characteristics TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=10\text{mA}, I_B=0$	400			V
Emitter Cut-off Current	I_{EBO}	$V_{EB}=9\text{V}, I_C=0$			1	mA
*DC Current Gain	h_{FE1} h_{FE2}	$V_{CE}=5\text{V}, I_C=1\text{A}$ $V_{CE}=5\text{V}, I_C=2\text{A}$	20 8		40	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=0.2\text{A}$ $I_C=2\text{A}, I_B=0.5\text{A}$ $I_C=4\text{A}, I_B=1\text{A}$			0.5 0.6 1	V V V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1\text{A}, I_B=0.2\text{A}$ $I_C=2\text{A}, I_B=0.5\text{A}$			1.2 1.6	V V
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, f=0.1\text{MHz}$		65		pF
Current Gain Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=0.5\text{A}$	4			MHz
Turn on Time	t_{on}	$V_{CC}=125\text{V}, I_C=2\text{A}$ $I_{B1}=0.4\text{A}, I_{B2}=-0.4\text{A}$ $R_L=62.5\Omega$			0.8	μS
Storage Time	t_{stg}				4.0	μS
Fall Time	t_F				0.9	μS

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycles $\leq 2\%$

PTU13005G / PTD13005G

Typical Characteristics

